EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

Fast Thyristor Type FDT80-2000-12

Low switching losses / Low reverse recovery charge
Distributed amplified gate for high di_T/dt

Mean on-state current		I_{TAV}	2000 A
Repetitive peak off-state voltage		V_{DRM}	1000...1200 V
Repetitive peak reverse voltage		V_{RRM}	
Turn-off time		t_q	10.0, 12.5, 16.0, 20.0 μs
V_{DRM}, V_{RRM}, V	1000		1200
Voltage code	10		12
T_j, °C	–60...+125		

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	2000 2376 3644	T_c=92 °C; Double side cooled; T_c=85 °C; Double side cooled; T_c=55 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	3140	T_c=92 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	65.0 75.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_D=V_R=0 V; Gate pulse:I_G=I_{FGM}; V_G=20 V; t_{GP}=50 μs; di_G/dt=2 A/μs
			68.0 78.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_D=V_R=0 V; Gate pulse:I_G=I_{FGM}; V_G=20 V; t_{GP}=50 μs; di_G/dt=2 A/μs
I^2t	Safety factor	$A^2s \cdot 10^3$	21100 28100	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_D=V_R=0 V; Gate pulse:I_G=I_{FGM}; V_G=20 V; t_{GP}=50 μs; di_G/dt=2 A/μs
			19100 25200	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_D=V_R=0 V; Gate pulse:I_G=I_{FGM}; V_G=20 V; t_{GP}=50 μs; di_G/dt=2 A/μs
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	1000...1200	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	1100...1300	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	0.6·V_{DRM} 0.6·V_{RRM}	T_j=$T_{j\,max}$; Gate open	

TRIGGERING				
I_{FGM}	Peak forward gate current	A	10	$T_j=T_{j\,max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	8	$T_j=T_{j\,max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/µs	2500	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; I_{TM}= 4000 A; Gate pulse: I_G=2 A; V_G=20 V; t_{GP}=50 µs; di_G/dt=2 A/µs
THERMAL				
T_{stg}	Storage temperature	°C	–60...+50	
T_j	Operating junction temperature	°C	–60...+125	
MECHANICAL				
F	Mounting force	kN	40.0...50.0	
a	Acceleration	m/s^2	50	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.15	T_j=25 °C; I_{TM}=6280 A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.456	$T_j=T_{j\,max}$; 0.5 π I_{TAV} < I_T < 1.5 π I_{TAV}	
r_T	On-state slope resistance, max	mΩ	0.090		
I_H	Holding current, max	mA	1000	T_j=25 °C; V_D=12 V; Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	300	$T_j=T_{j\,max}$; $V_D=V_{DRM}$; $V_R=V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage[1], min	V/µs	200, 320, 500, 1000, 1600, 2000, 2500	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00 3.00 1.50	T_j= $T_{j\,min}$ T_j=25 °C T_j= $T_{j\,max}$	V_D=12 V; I_D=3 A; Direct gate current
I_{GT}	Gate trigger direct current, max	mA	500 300 150	T_j= $T_{j\,min}$ T_j= 25 °C T_j= $T_{j\,max}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.35	$T_j=T_{j\,max}$; $V_D=0.67\cdot V_{DRM}$; Direct gate current	
I_{GD}	Gate non-trigger direct current, min	mA	65.00		
SWITCHING					
t_{gd}	Delay time, max	µs	0.80	T_j=25 °C; V_D=600 V; $I_{TM}=I_{TAV}$; di/dt=200 A/µs; Gate pulse: I_G=2 A; V_G=20 V; t_{GP}=50 µs; di_G/dt=2 A/µs	
t_{gt}	Turn-on time[2], max	µs	1.60, 2.00, 2.50, 3.20		
t_q	Turn-off time[3] max	µs	10.0, 12.5, 16.0, 20.0	dv_D/dt=50 V/µs;	$T_j=T_{j\,max}$; $I_{TM}=I_{TAV}$; di_R/dt=-10 A/µs; V_R=100V; V_D=0.67 V_{DRM}
			12.5, 16.0, 20.0, 25.0	dv_D/dt=200 V/µs;	
Q_{rr}	Total recovered charge, max	µC	220	$T_j=T_{j\,max}$; I_{TM}=2000 A; di_R/dt=-50 A/µs; V_R=100 V	
t_{rr}	Reverse recovery time, max	µs	3.8		
I_{rrM}	Peak reverse recovery current, max	A	115		

THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0085	Direct current	Double side cooled
R_{thjc-A}			0.0187		Anode side cooled
R_{thjc-K}			0.0153		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0020	Direct current	
MECHANICAL					
w	Weight, max	g	1170		
D_s	Surface creepage distance	mm (inch)	36.60 (1.441)		
D_a	Air strike distance	mm (inch)	16.20 (0.638)		

PART NUMBERING GUIDE

FDT	80	2000	12	7	8	4	
1	2	3	4	5	6	7	

1. FDT — Fast Inverter Disc Thyristor
2. Design version
3. Mean on-state current, A
4. Voltage code
5. Critical rate of rise of off-state voltage
6. Group of turn-off time (dv_D/dt=50 V/μs)
7. Group of turn-on time

NOTES

1) Critical rate of rise of off-state voltage

Symbol of Group	4	5	6	7	8	8,5	9
$(dv_D/dt)_{crit}$, V/μs	200	320	500	1000	1600	2000	2500

2) Turn-on time

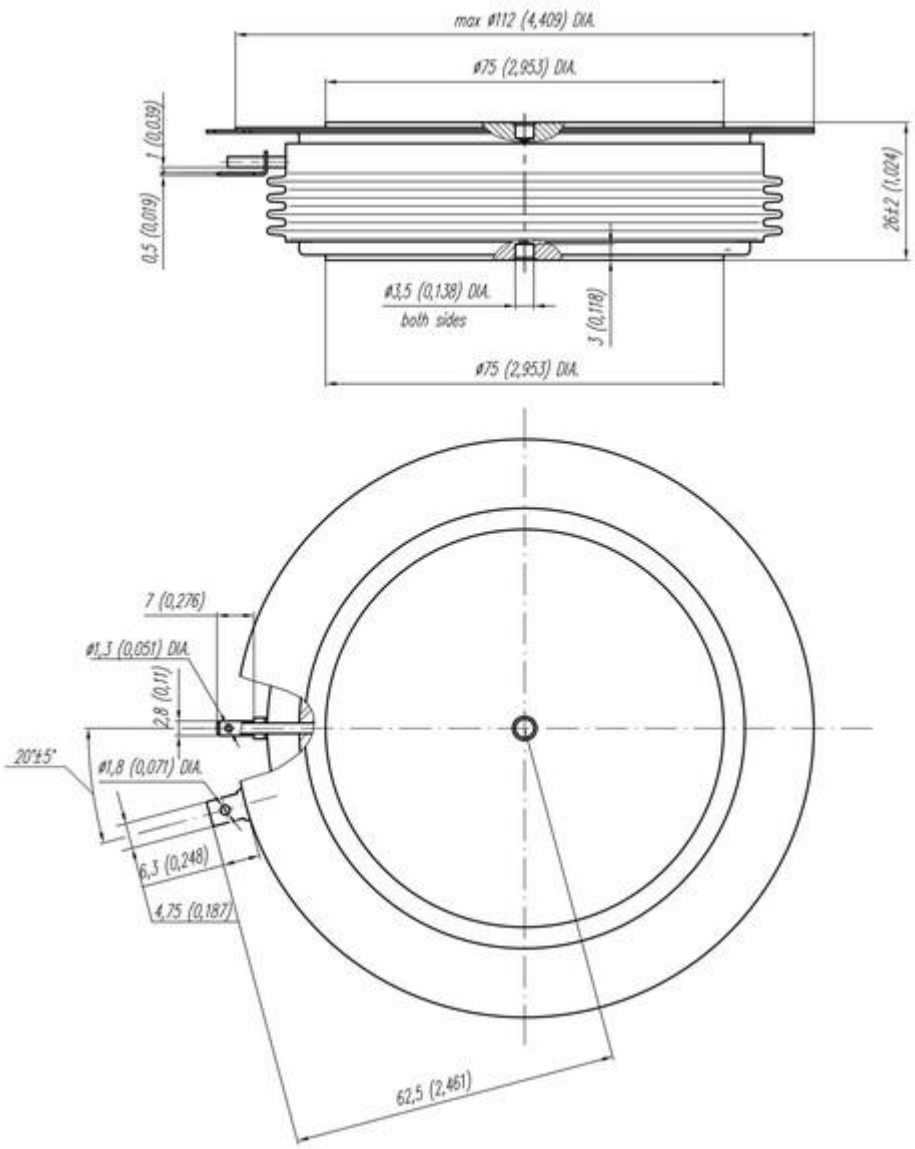
Symbol of group	6	5	4	3
t_{gt}, μs	1.60	2.00	2.50	3.20

3) Turn-off time (dv_D/dt=50 V/μs)

Symbol of group	8.5	8	7	6
t_q, μs	10.0	12.5	16.0	20.0

OVERALL DIMENSIONS

Package type: T.F2



All dimensions in millimeters (inches)